AMENDMENTS TO THE SPECIFICATION:

Please replace the second full paragraph on page 3 with the following amended paragraph:

As in the above, the dual damascene process for first forming the trench is simple and has a less problem in the etching process than the dual damascene process. Accordingly, this process has been recognized one of the methods having a high reproducibility. However, from the viewpoint of the lithography, the dual damascene process that first forms the trench ~~than~~ then the via hole must form a second photoresist pattern for defining the via hole region with the step generated by the trench. For this reason, there is a problem that resolution is fatally influenced since the photoresist pattern is thickly formed in the trench region, as in FIG. 1(c). Accordingly, it is recently recognized that this process is rarely used since it is difficult to overcome the above problem.

Please replace the paragraph bridging page 4 and page 5 with the following amended paragraph:

To achieve these objects and other advantages and in accordance with the purpose of the invention, as embodied and broadly described herein, a method of forming a dual damascene pattern in a semiconductor device according to the present invention is characterized in that it comprises the steps of

providing a semiconductor substrate in which an interlayer insulating film is formed and a trench of a given pattern is formed in the interlayer insulating film, forming a photoresist pattern in which a via hole region is defined, in the trench, forming a high polymer solution coating film containing a crosslinkable agent or a radical generator, on the entire structure, reacting to the crosslinkable agent or the radical generator with polymer of the photoresist pattern by means of a baking process so that an etching tolerance property is increased, thereby forming a hardened photoresist pattern, removing the high polymer solution coating film, and forming a via hole in the interlayer insulating film by means of an etching process, wherein the photoresist pattern is thinly formed relatively as ~~mush~~ much as the etching tolerance property is increased by the hardened photoresist pattern.

Please replace the second full paragraph on page 7 with the following amended paragraph:

With reference to FIG. 2c, a resist is coated on the interlayer insulating film 202. A second photoresist pattern 205 in which a via hole region is defined is formed through the exposure and development processes. At this time, if the second photoresist pattern 205 is thickly formed in the region where the trench is formed, resolution may be degraded in the exposure and development process. In order to prevent this, it is required that

the second photoresist pattern 205 be formed widely ~~by maximum~~. Meanwhile, if the second photoresist pattern 205 is too thinly formed, the surface of the semiconductor substrate 201 ~~may be experienced by etch damage~~ may be damaged by an etch as the second photoresist pattern formed on the semiconductor substrate 201 is removed, in a subsequent etching process for forming the via hole. Accordingly, the thickness of the second photoresist pattern 205 is decided considering an etching tolerance property of a hardened stat in a subsequent process.

Please replace the paragraph bridging page 7 and page 8 with the following amended paragraph:

~~Turing~~ Turning to FIG. 2d, a high polymer solution is coated on the entire structure by means of a spin coating method in order to harden the second photoresist pattern 205, thereby forming a high polymer solution coating film 206. At this time, the high polymer solution employs a high polymer solution containing a crosslinkable agent or a radical generator. In this case, the high polymer solution used employs an aqueous high polymer solution so that it is similar to a top anti-reflective coating film (not shown) that is usually used in the lithography process. The high polymer solution uses DI water as a solvent. In case of the aqueous high polymer solution using water as the solvent, it could be coated while preventing mixing with the second photoresist

pattern 205 such as the existing top anti-reflective coating film in case of a double coating.